

Description

The VSM55N04 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

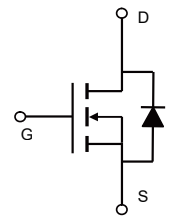
- $V_{DS}=45V, I_D=55A$
 $R_{DS(ON)}=9.2m\Omega @ V_{GS}=10V$ (Typ)
 $R_{DS(ON)}=13m\Omega @ V_{GS}=4.5V$ (Typ)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply



TO-252



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM55N04	VSM55N04-T2	TO-252	-	-	-

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	45	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	55	A
Pulsed Drain Current	I_{DM}	220	A
Maximum Power Dissipation	P_D	75	W
Derating factor		0.5	W/ $^\circ\text{C}$
Single pulse avalanche energy ^(Note 5)	E_{AS}	145	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.0	$^\circ\text{C/W}$
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Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

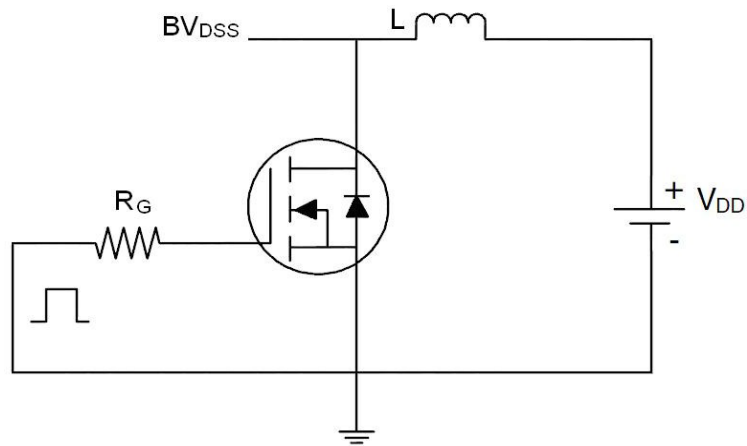
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	45	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =45V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	9.2	11	mΩ
		V _{GS} =4.5V, I _D =20A	-	13	17	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =20A	-	35	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	1150	-	PF
Output Capacitance	C _{OSS}		-	135	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	125	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =1Ω V _{GS} =10V, R _G =3Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	17	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	17	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	32.5		nC
Gate-Source Charge	Q _{gs}		-	3.6		nC
Gate-Drain Charge	Q _{gd}		-	9.6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	55	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A di/dt = 100A/μs ^(Note3)	-	29	-	nS
Reverse Recovery Charge	Q _{rr}		-	26	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

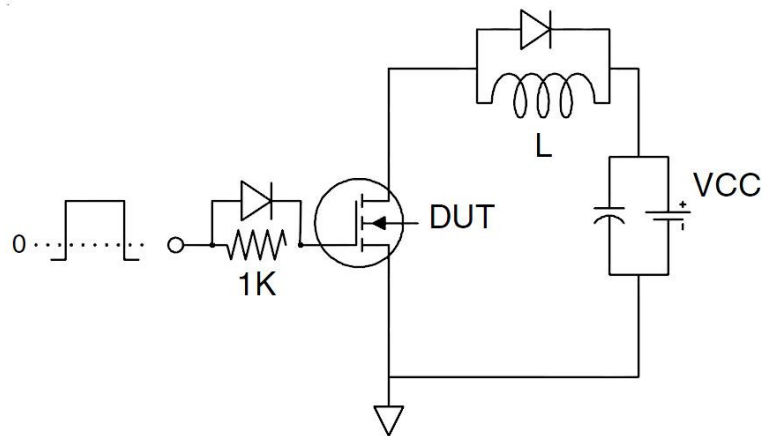
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}\text{C}$. The Power dissipation PDSM is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=0.5mH, R_G=25\Omega$.

Test circuit

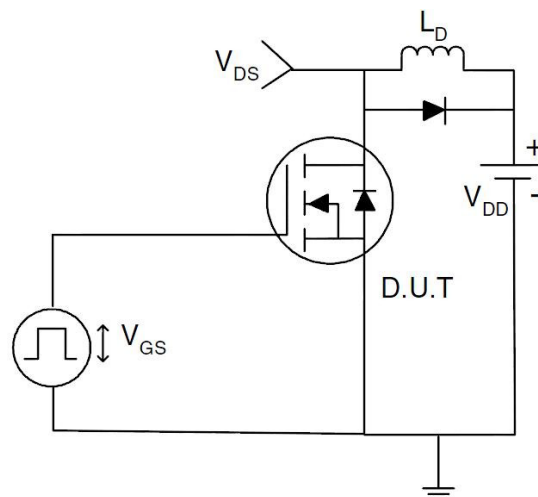
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

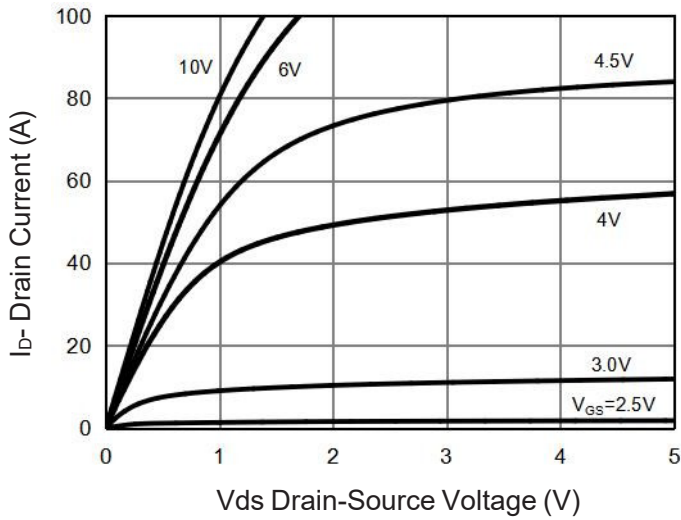


Figure 1 Output Characteristics

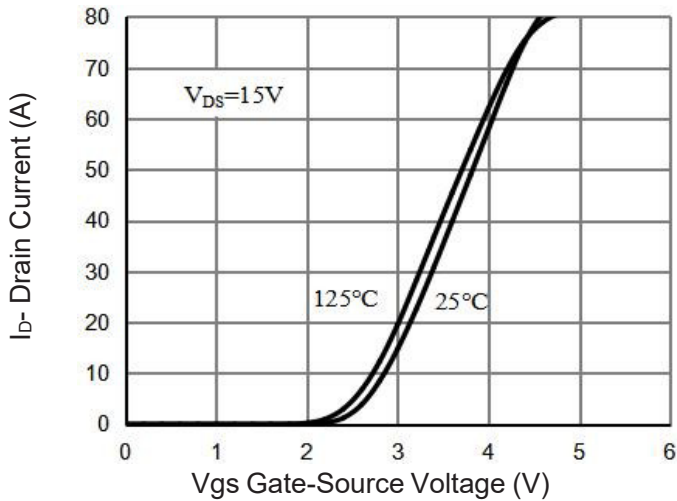


Figure 2 Transfer Characteristics

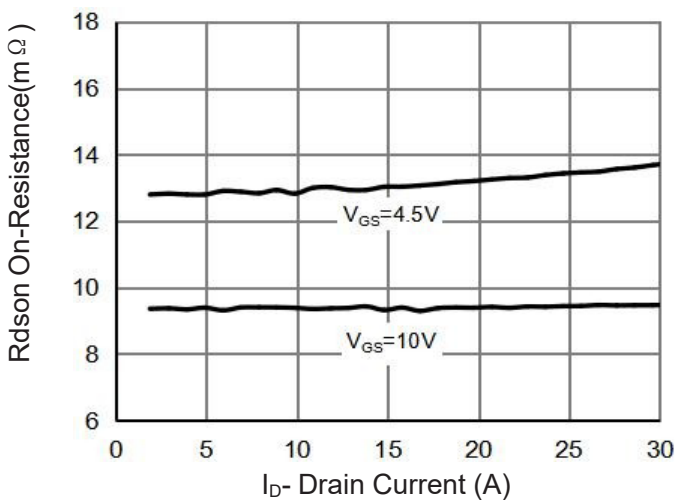


Figure 3 Rdson- Drain Current

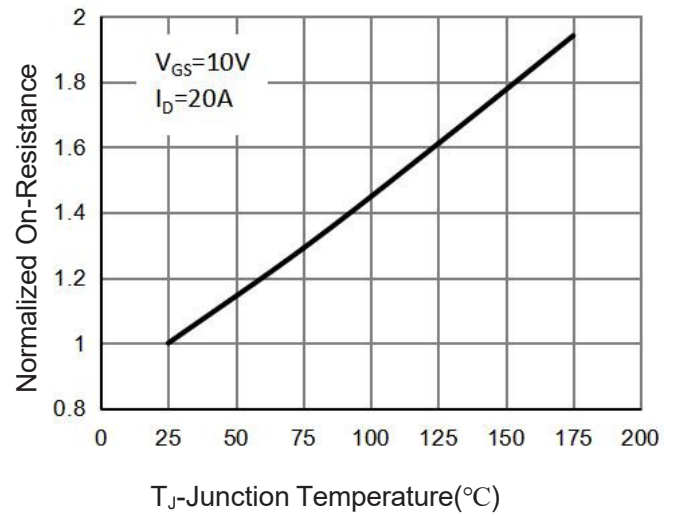


Figure 4 Rdson-Junction Temperature

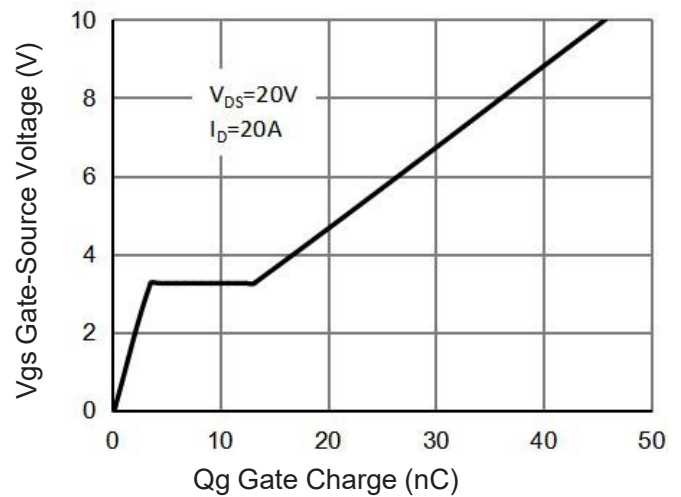


Figure 5 Gate Charge

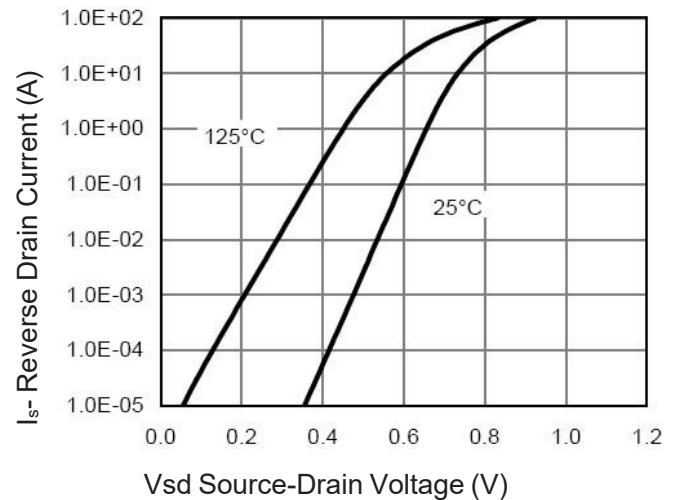
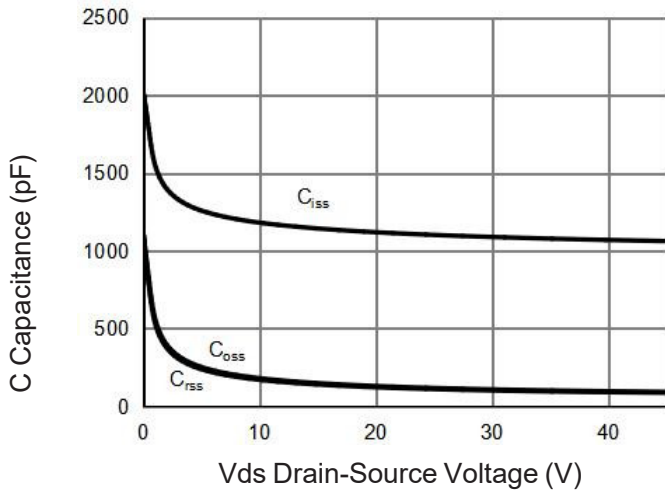
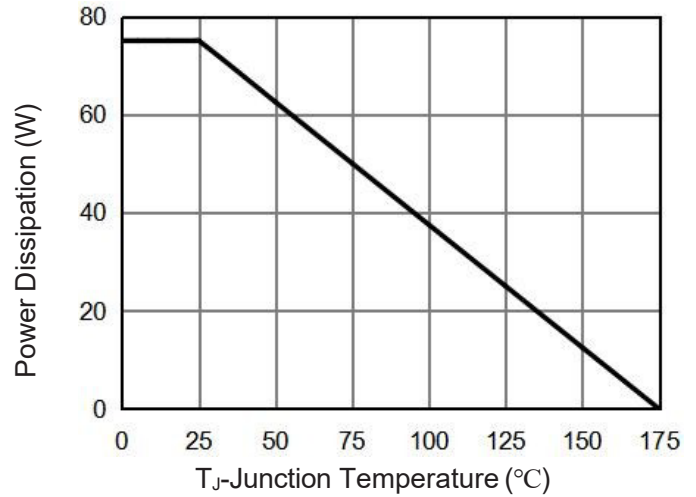
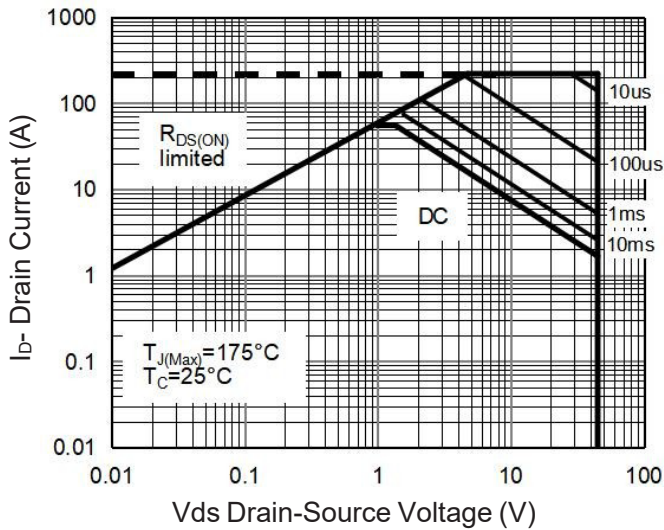
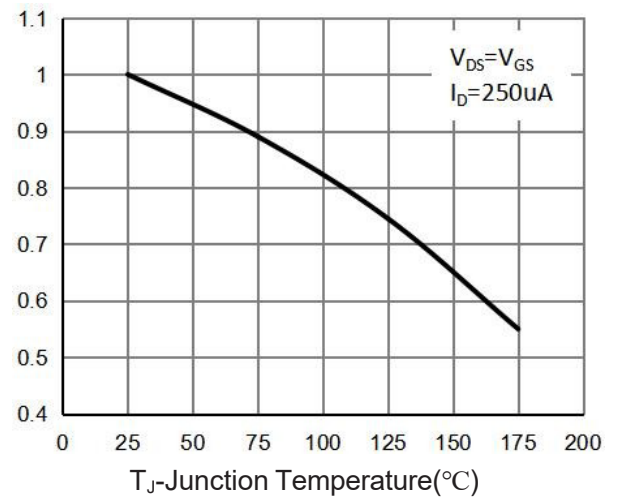
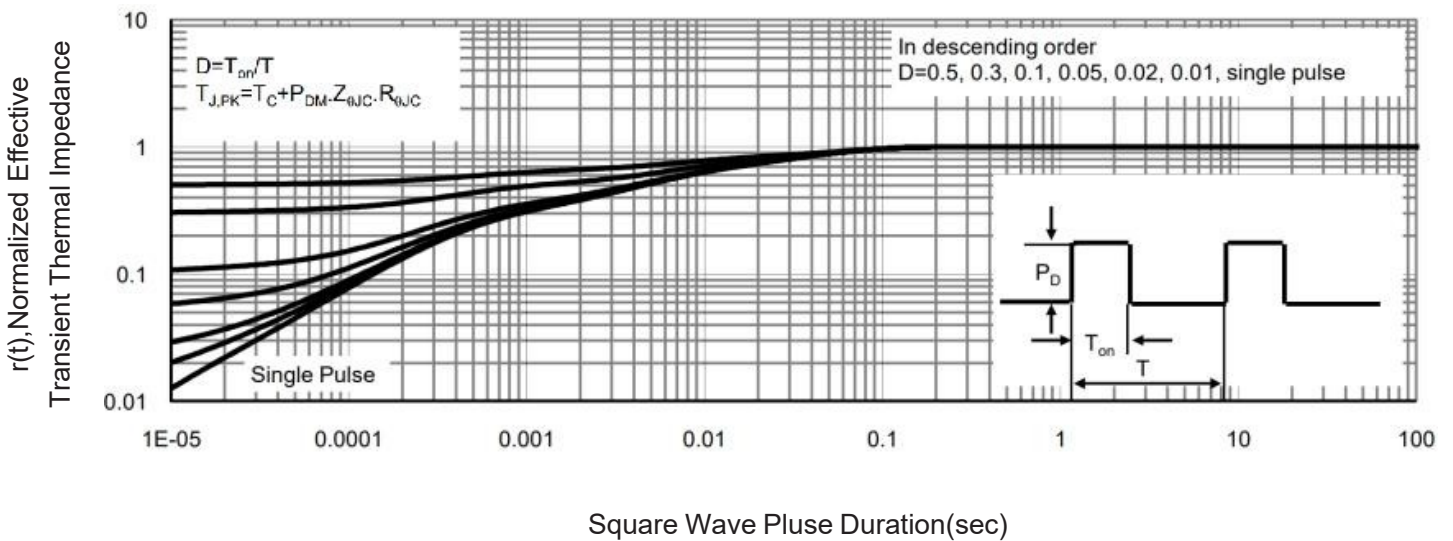


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 $V_{GS(th)}$ vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance